

# General Purpose Transistor

## NPN Silicon

### MMBT2222AWT1G, SMMBT2222AWT1G

These transistors are designed for general purpose amplifier applications. They are housed in the SOT-323/SC-70 package which is designed for low power surface mount applications.

#### Features

- AEC-Q101 Qualified and PPAP Capable
- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant\*

#### MAXIMUM RATINGS

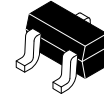
Rating	Symbol	Value	Unit
Collector - Emitter Voltage	$V_{CEO}$	40	Vdc
Collector - Base Voltage	$V_{CBO}$	75	Vdc
Emitter - Base Voltage	$V_{EBO}$	6.0	Vdc
Collector Current - Continuous	$I_C$	600	mAdc

#### THERMAL CHARACTERISTICS

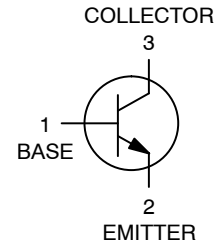
Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board $T_A = 25^\circ\text{C}$	$P_D$	150	mW
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	280	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

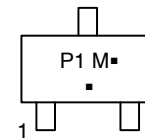
\*For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



SC-70  
CASE 419  
STYLE 3



#### MARKING DIAGRAM



- P1 = Specific Device Code
- M = Date Code
- = Pb-Free Package

(Note: Microdot may be in either location)

#### ORDERING INFORMATION

Device	Package	Shipping†
MMBT2222AWT1G	SC-70 (Pb-Free)	3,000 / Tape & Reel
SMMBT2222AWT1G	SC-70 (Pb-Free)	3,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

# MMBT2222AWT1G, SMMBT2222AWT1G

## ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
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### OFF CHARACTERISTICS

Collector – Emitter Breakdown Voltage (Note 1) ( $I_C = 10\text{ mA}$ , $I_B = 0$ )	$V_{(BR)CEO}$	40	–	Vdc
Collector – Base Breakdown Voltage ( $I_C = 10\text{ }\mu\text{A}$ , $I_E = 0$ )	$V_{(BR)CBO}$	75	–	Vdc
Emitter – Base Breakdown Voltage ( $I_E = 10\text{ }\mu\text{A}$ , $I_C = 0$ )	$V_{(BR)EBO}$	6.0	–	Vdc
Base Cutoff Current ( $V_{CE} = 60\text{ Vdc}$ , $V_{EB} = 3.0\text{ Vdc}$ )	$I_{BL}$	–	20	nAdc
Collector Cutoff Current ( $V_{CE} = 60\text{ Vdc}$ , $V_{EB} = 3.0\text{ Vdc}$ )	$I_{CEX}$	–	10	nAdc

### ON CHARACTERISTICS (Note 1)

DC Current Gain (Note 1) ( $I_C = 0.1\text{ mA}$ , $V_{CE} = 10\text{ Vdc}$ ) ( $I_C = 1.0\text{ mA}$ , $V_{CE} = 10\text{ Vdc}$ ) ( $I_C = 10\text{ mA}$ , $V_{CE} = 10\text{ Vdc}$ ) ( $I_C = 150\text{ mA}$ , $V_{CE} = 10\text{ Vdc}$ ) ( $I_C = 500\text{ mA}$ , $V_{CE} = 10\text{ Vdc}$ )	$H_{FE}$	35 50 75 100 40	– – – 300 –	–
Collector – Emitter Saturation Voltage (Note 1) ( $I_C = 150\text{ mA}$ , $I_B = 15\text{ mA}$ ) ( $I_C = 500\text{ mA}$ , $I_B = 50\text{ mA}$ )	$V_{CE(sat)}$	– –	0.3 1.0	Vdc
Base – Emitter Saturation Voltage (Note 1) ( $I_C = 150\text{ mA}$ , $I_B = 15\text{ mA}$ ) ( $I_C = 500\text{ mA}$ , $I_B = 50\text{ mA}$ )	$V_{BE(sat)}$	0.6 –	1.2 2.0	Vdc

### SMALL-SIGNAL CHARACTERISTICS

Current – Gain – Bandwidth Product ( $I_C = 20\text{ mA}$ , $V_{CE} = 20\text{ Vdc}$ , $f = 100\text{ MHz}$ )	$f_T$	300	–	MHz
Output Capacitance ( $V_{CB} = 10\text{ Vdc}$ , $I_E = 0$ , $f = 1.0\text{ MHz}$ )	$C_{obo}$	–	8.0	pF
Input Capacitance ( $V_{EB} = 0.5\text{ Vdc}$ , $I_C = 0$ , $f = 1.0\text{ MHz}$ )	$C_{ibo}$	–	30	pF
Input Impedance ( $V_{CE} = 10\text{ Vdc}$ , $I_C = 10\text{ mA}$ , $f = 1.0\text{ kHz}$ )	$h_{ie}$	0.25	1.25	k $\Omega$
Voltage Feedback Ratio ( $V_{CE} = 10\text{ Vdc}$ , $I_C = 10\text{ mA}$ , $f = 1.0\text{ kHz}$ )	$h_{re}$	–	4.0	$\times 10^{-4}$
Small – Signal Current Gain ( $V_{CE} = 10\text{ Vdc}$ , $I_C = 10\text{ mA}$ , $f = 1.0\text{ kHz}$ )	$h_{fe}$	75	375	–
Output Admittance ( $V_{CE} = 10\text{ Vdc}$ , $I_C = 10\text{ mA}$ , $f = 1.0\text{ kHz}$ )	$h_{oe}$	25	200	$\mu\text{mhos}$
Noise Figure ( $V_{CE} = 10\text{ Vdc}$ , $I_C = 100\text{ }\mu\text{A}$ , $R_S = 1.0\text{ k}\Omega$ , $f = 1.0\text{ kHz}$ )	NF	–	4.0	dB

### SWITCHING CHARACTERISTICS

Delay Time	$(V_{CC} = 3.0\text{ Vdc}$ , $V_{BE} = -0.5\text{ Vdc}$ , $I_C = 150\text{ mA}$ , $I_{B1} = 15\text{ mA}$ )	$t_d$	–	10	ns
Rise Time		$t_r$	–	25	
Storage Time	$(V_{CC} = 30\text{ Vdc}$ , $I_C = 150\text{ mA}$ , $I_{B1} = I_{B2} = 15\text{ mA}$ )	$t_s$	–	225	ns
Fall Time		$t_f$	–	60	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. Pulse Test: Pulse Width  $\leq 300\text{ }\mu\text{s}$ , Duty Cycle  $\leq 2.0\%$ .

# MMBT2222AWT1G, SMMBT2222AWT1G

## SWITCHING TIME EQUIVALENT TEST CIRCUITS

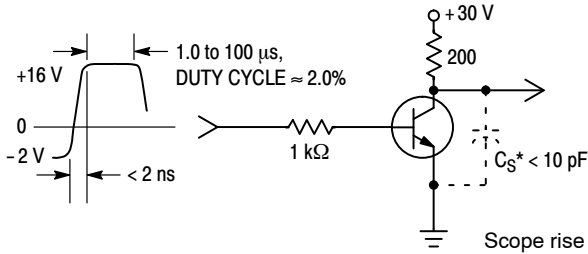


Figure 1. Turn-On Time

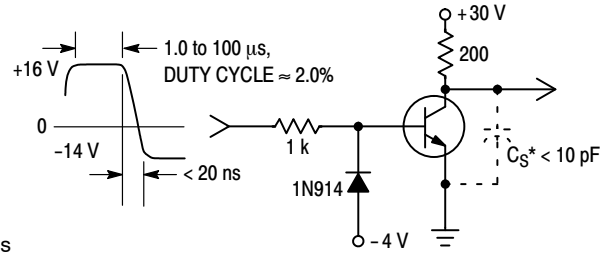


Figure 2. Turn-Off Time

Scope rise time <math>< 4 \text{ ns}</math>  
 \*Total shunt capacitance of test jig, connectors, and oscilloscope.

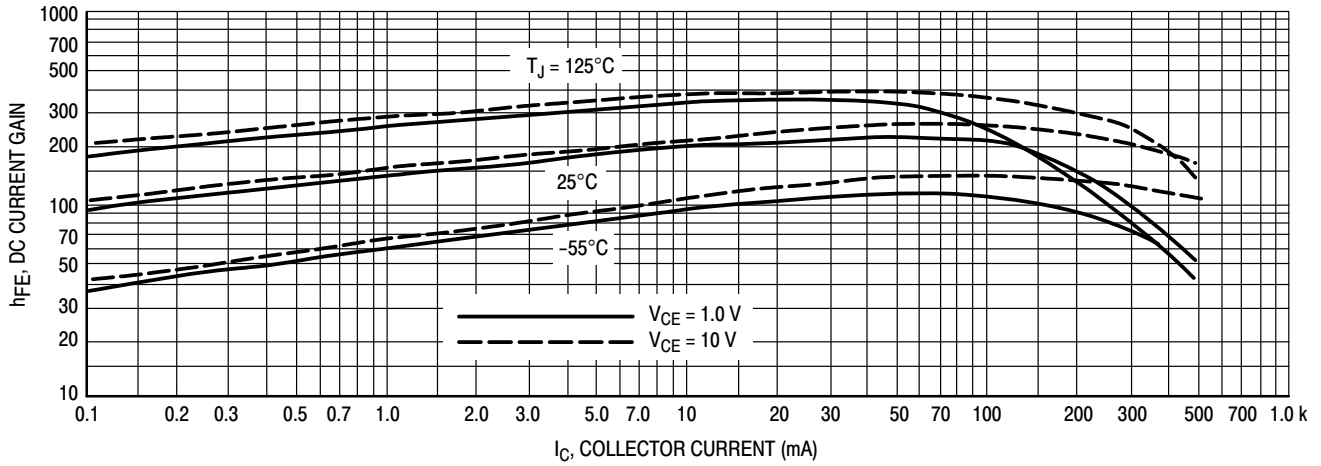


Figure 3. DC Current Gain

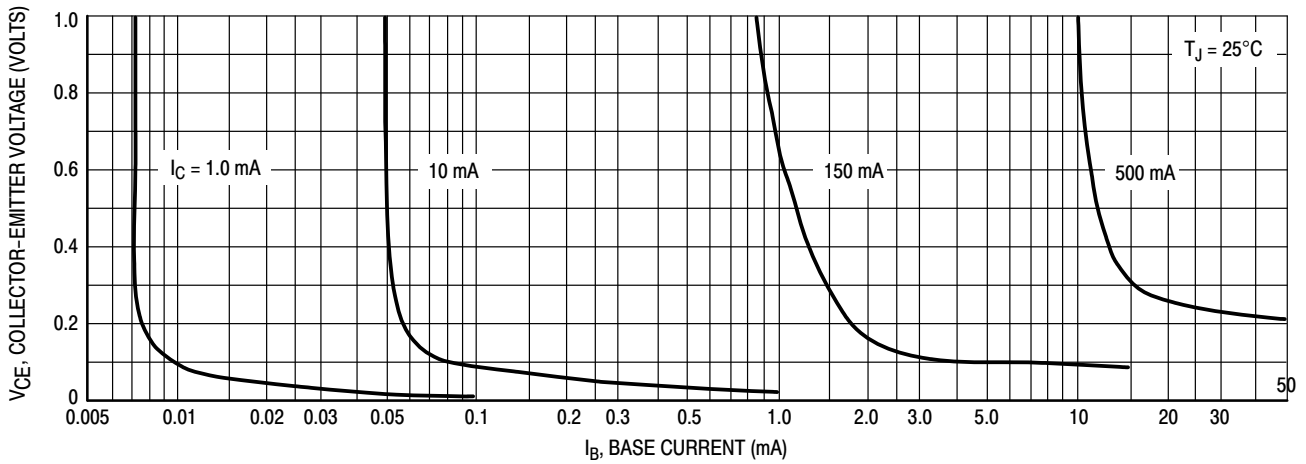


Figure 4. Collector Saturation Region

# MMBT2222AWT1G, SMMBT2222AWT1G

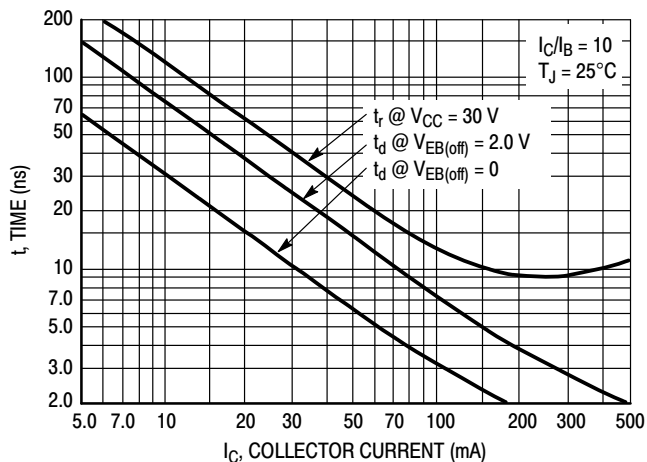


Figure 5. Turn-On Time

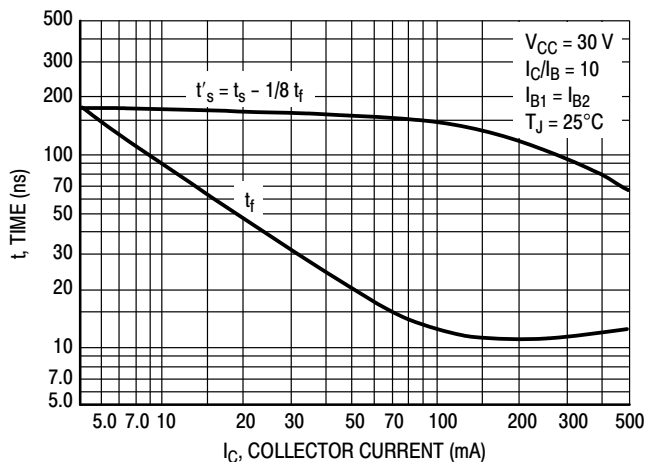


Figure 6. Turn-Off Time

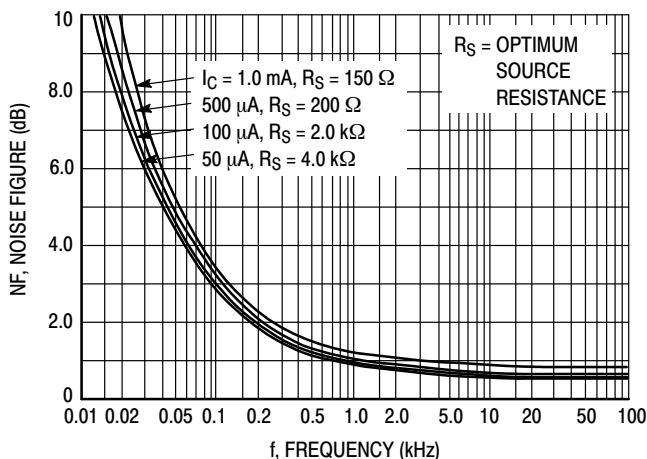


Figure 7. Frequency Effects

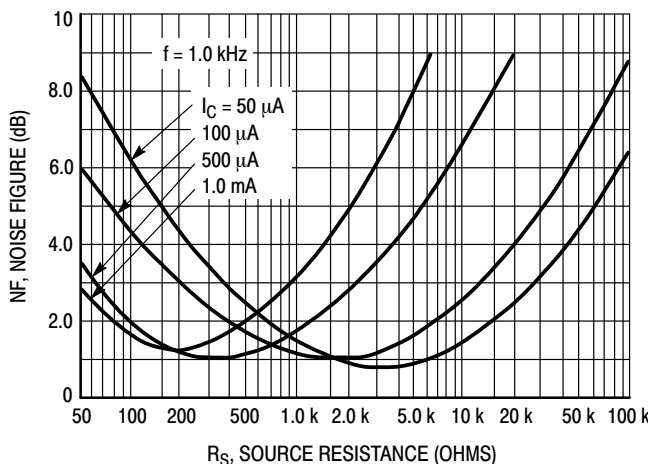


Figure 8. Source Resistance Effects

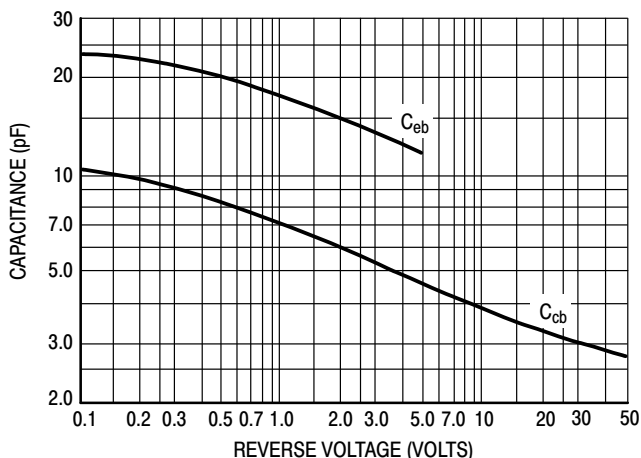


Figure 9. Capacitances

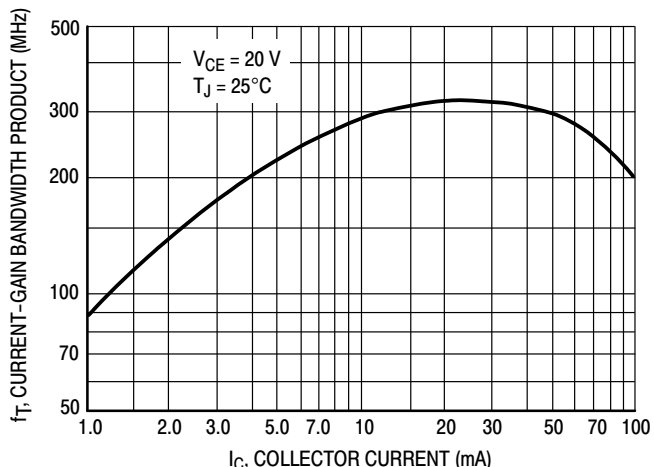
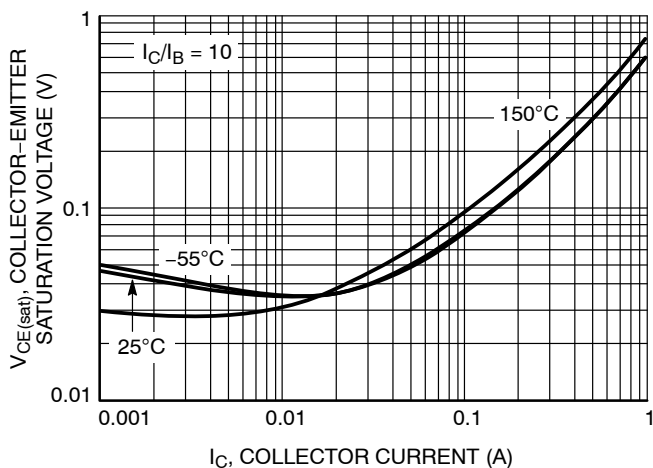
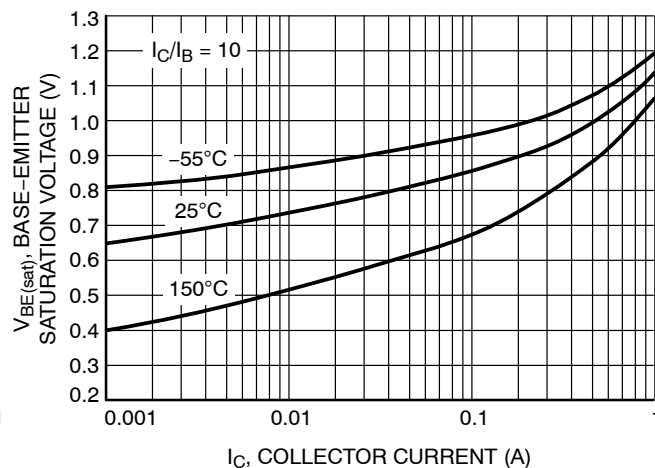


Figure 10. Current-Gain Bandwidth Product

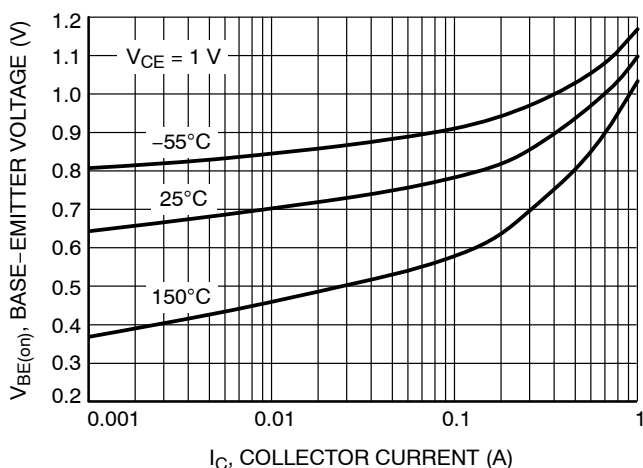
# MMBT2222AWT1G, SMMBT2222AWT1G



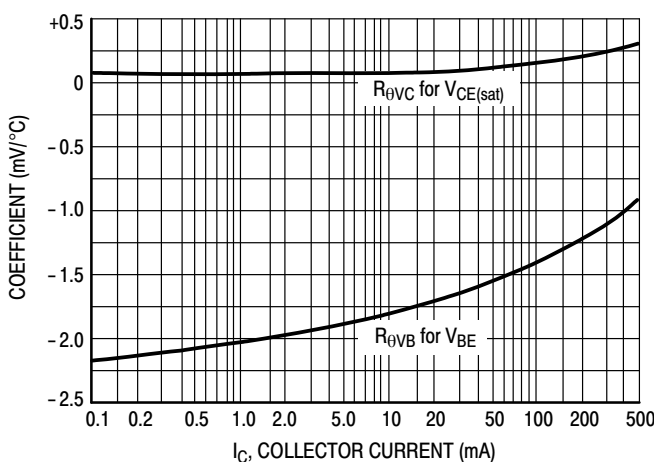
**Figure 11. Collector Emitter Saturation Voltage vs. Collector Current**



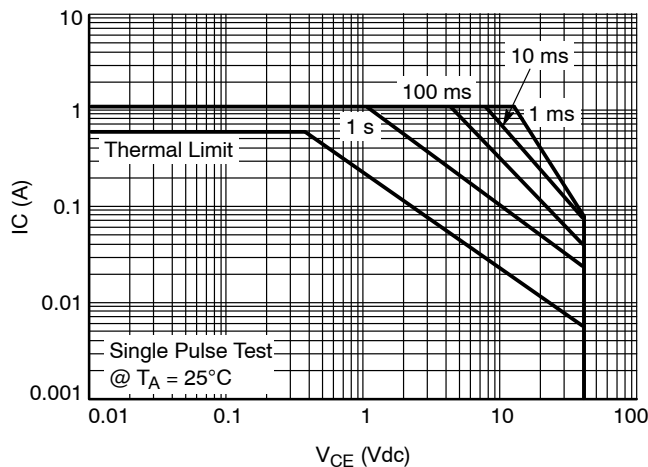
**Figure 12. Base Emitter Saturation Voltage vs. Collector Current**



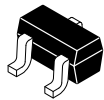
**Figure 13. Base Emitter Voltage vs. Collector Current**



**Figure 14. Temperature Coefficients**



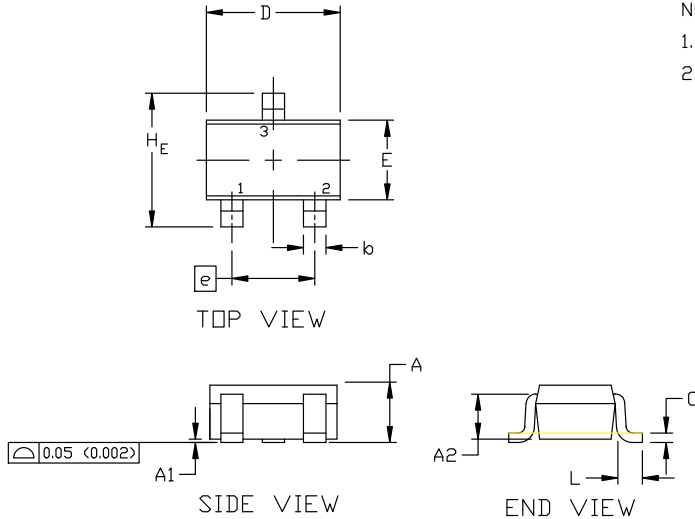
**Figure 15. Safe Operating Area**



SCALE 4:1

SC-70 (SOT-323)  
CASE 419  
ISSUE R

DATE 11 OCT 2022

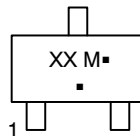


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH

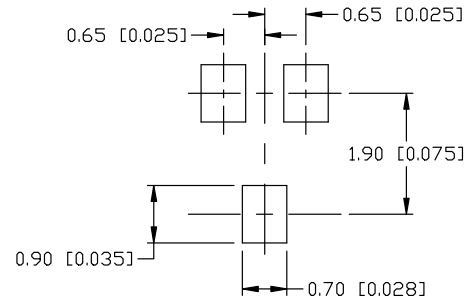
DIM	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2	0.70 REF			0.028 BSC		
b	0.30	0.35	0.40	0.012	0.014	0.016
c	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.00	2.20	0.071	0.080	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
e	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65 BSC			0.026 BSC		
L	0.20	0.38	0.56	0.008	0.015	0.022
H <sub>E</sub>	2.00	2.10	2.40	0.079	0.083	0.095

GENERIC MARKING DIAGRAM



- XX = Specific Device Code
- M = Date Code
- = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.



\* For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

SOLDERING FOOTPRINT

- |   |   |   |  |   |   |
|---|---|---|--|---|---|
| STYLE 1:<br>CANCELLED                                 | STYLE 2:<br>PIN 1. ANODE<br>2. N.C.<br>3. CATHODE     | STYLE 3:<br>PIN 1. BASE<br>2. EMITTER<br>3. COLLECTOR | STYLE 4:<br>PIN 1. CATHODE<br>2. CATHODE<br>3. ANODE       | STYLE 5:<br>PIN 1. ANODE<br>2. ANODE<br>3. CATHODE          |   |
| STYLE 6:<br>PIN 1. EMITTER<br>2. BASE<br>3. COLLECTOR | STYLE 7:<br>PIN 1. BASE<br>2. EMITTER<br>3. COLLECTOR | STYLE 8:<br>PIN 1. GATE<br>2. SOURCE<br>3. DRAIN      | STYLE 9:<br>PIN 1. ANODE<br>2. CATHODE<br>3. CATHODE-ANODE | STYLE 10:<br>PIN 1. CATHODE<br>2. ANODE<br>3. ANODE-CATHODE | STYLE 11:<br>PIN 1. CATHODE<br>2. CATHODE<br>3. CATHODE |

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DESCRIPTION:	SC-70 (SOT-323)	PAGE 1 OF 1

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